Attorney Docket: MXIC 1553-3

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re application of:

Chih C. YEH et al. Group Art Unit: 2818

Application No. 10/642,249 Examiner: Unassigned

Confirmation No.: 1545

Customer No. 22470

Filed: 15 August 2003

Title: Method for Programming **Programmable Eraseless Memory** 

## FOURTH SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

It is requested that the information identified in this statement be considered by the Examiner and made of record in the above-identified application. This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in 37 C.F.R. 1.56.

Enclosed with this statement is Form PTO/SB/O8A. The Examiner is requested to initial the form and return it to the undersigned in accordance with M.P.E.P. 609.

Also enclosed with this statement is a copy of each cited document as required by 37 C.F.R. 1.98. The exception to this, in accordance with the 05 August 2003 Official Gazette Notice in which the USPTO waives the requirement for submitting copies of U.S. Patent and Publications for cases filed after 30 June 2003, is that copies of U.S. Patent documents and copies of U.S. Patent publications are not being submitted.

This statement should be considered under 37 C.F.R. 1.97(b) because it is being filed before the mailing date of the first Office Action on the merits.

Attorney Docket: MXIC 1553-3

Fee Authorization. The Commissioner is hereby authorized to charge underpayment of any additional fees or credit any overpayment associated with this communication to Deposit Account No. 50-0869 (MXIC 1553-3). A duplicate copy of this authorization is enclosed.

Respectfully submitted,

Date:

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By: Mark A. Haynes, Reg. No. 30,846

PTO/SB/08A (08-03)

Approved for use through 07/31/2006. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Complete if Known

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Filing Date

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

of 2

First Named Inventor Art Unit 2818

**Application Number** 

Examiner Name

10/642,249 15 August 2003 Chih C. Yeh et al. Unassigned

(Use as many sheets as necessary)

Substitute for form 1449/PTO

Sheet 1

MXIC 1553-3 Attorney Docket Number

			U. S. PATENT	DOCUMENTS		
Examiner Initials*	Cite No.1	Document Number  Number-Kind Code <sup>2 (d known)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
	A1	US- 6,650,143	11-18-2003	Peng		
				<u> </u>		
	A2	<sup>US-</sup> 6,667,902	12-23-2003	Peng		
	A3	<sup>US-</sup> 6,671,040	12-30-2003	Fong et al.		
	A4	<sup>US-</sup> 6,700,151	03-02-2004	Peng		
	A5	<sup>US-</sup> 2002/0094611	07-17-2002	Wu et al.	•	
	A6	<sup>US-</sup> 2004/0008538	01-15-2004	Peng		
	A7	<sup>US-</sup> 2004/0047218	03-11-2004	Peng		
	A8	<sup>US-</sup> 2004/0106251	06-03-2004	Forbes et al.		
	A9	<sup>US-</sup> 2004/0129995	07-08-2004	Yeo et al.		
	A10	<sup>US-</sup> 2004/0137688	07-15-2004	Chang et al.		
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	Γ	
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Examiner	Date	
Signature	Considered	

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Translation is attached.

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Substitute for form 1449/PTO				Complete if Known			
				Application Number	10/642,249		
INF	ORMATION	DIS	CLOSURE	Filing Date	15 August 2003		
STATEMENT BY APPLICANT			PPLICANT	First Named Inventor	Chih C. Yeh et al.		
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Sheet	2	of	2	Attorney Docket Number	MXIC 1553-3		

Examiner	Cite	NON PATENT LITERATURE DOCUMENTS  Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of	
Initials*	No.1	the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	C1	Stathis, J.H., "Reliability Limits for the Gate Insulator in CMOS Technology" IBM. J. Res. & Dev., Vol. 46, No. 2/3, March/May 2002, 265-286	
	C2	Miranda, Enrique, et al. "Analytic Modeling of Leakage Current Through Multiple Breakdown Paths in SiO2 Films" IEEE 39th Annual IRPS 2001, 367-379	
	СЗ	Wu, E.Y. et al., "Voltage-Dependent Voltage-Acceleration of Oxide Breakdown for Ultra- Thin Oxides" Electron Devices Meeting, 2000, IEDM Technical Digest International, 10- 13 December 2000, 541-544	
	C4	Sune, Jordi et al. "Post Soft Breakdown Conduction in SiO2 Gate Oxides" Electron Devices Meeting, 2000 IEDM Technical Digest International, 10-13 Dec. 2000 533-536	
	C5	Rasras, Mahmoud et al. "Substrate Hole Current Origin After Oxide Breakdown" Electron Devices Meeting, 2000 IEDM Technical Digest International, 10-13 Dec. 2000, 537-540	
	C6	Lombardo, S., et al. "Softening of Breakdown in Ultra-Thin Gate Oxide nMOSFETs at Low Inversion Layer Density" Reliability Physics Symposium 2001, Proceedings 39th Annual 2001 IEEE International, 30 April, 3 May 2001, 163-167	
	C7	Monsieur, F., et al. "A Thorough Investigation of Progressive Breakdown in Ultra-Thin Oxides Physical Understanding and Application for Industrial Reliability Assessment", Reliability Physics Symposium Proceedings 2002, 40th Annual 7-11 April 2000, 45-54	
	C8	Suehle, J. "Ultra-Thin Gate Oxide Reliability and Implications for Qualification, Design and Use in Ionizing Radiation Environments" NASA Microelectronics Reliability and Qualification Workshop, Manhattan Beach Marriott, Manhattan Beach, CA 12/3/02 30 pgs	

Examiner	 Date	
Signature	Considered	

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